



BME 202 Electronics

Lecture 11: FET Biasing

Common FET Biasing Circuits

JFET Biasing Circuits

Fixed-Bias

Self-Bias

Voltage-Divider Bias

D-Type MOSFET Biasing Circuits

Self-Bias

Voltage-Divider Bias

E-Type MOSFET Biasing Circuits

Feedback Configuration

Voltage-Divider Bias

Basic Current Relationships

For all FETs:

$$I_G \cong 0 \text{ A} \quad I_D = I_S$$

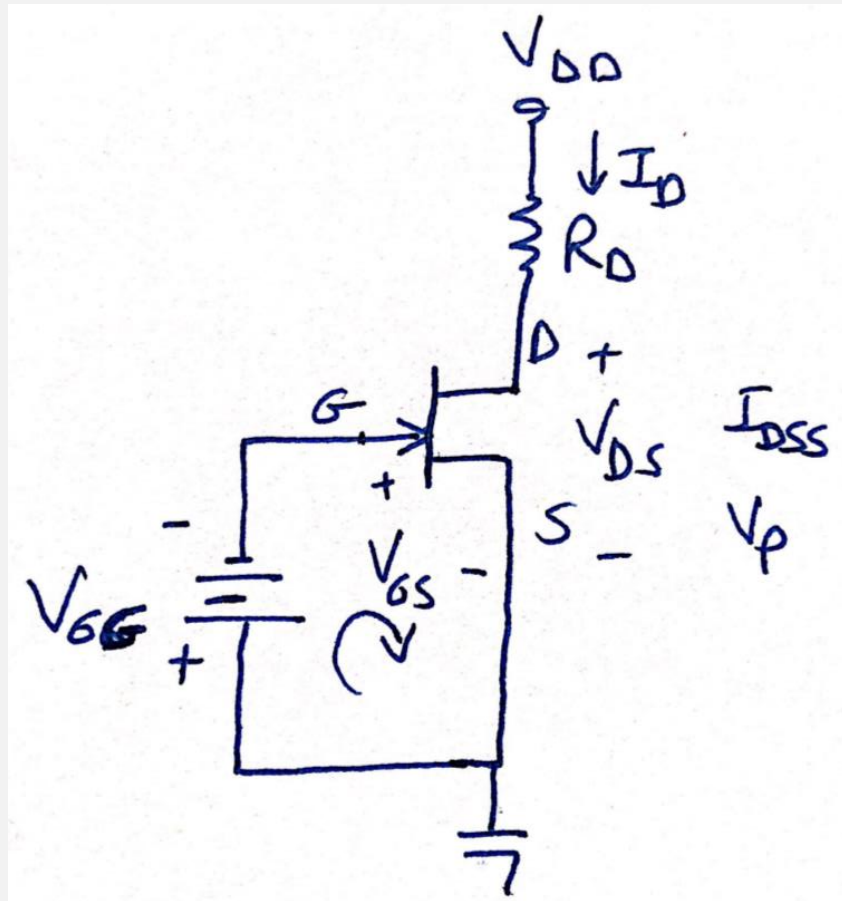
For JFETs and D-Type MOSFETs:

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2$$

For E-Type MOSFETs:

$$I_D = k(V_{GS} - V_T)^2$$

Fixed-Bias Configuration



$$V_{DS} = V_{DD} - I_D R_D$$

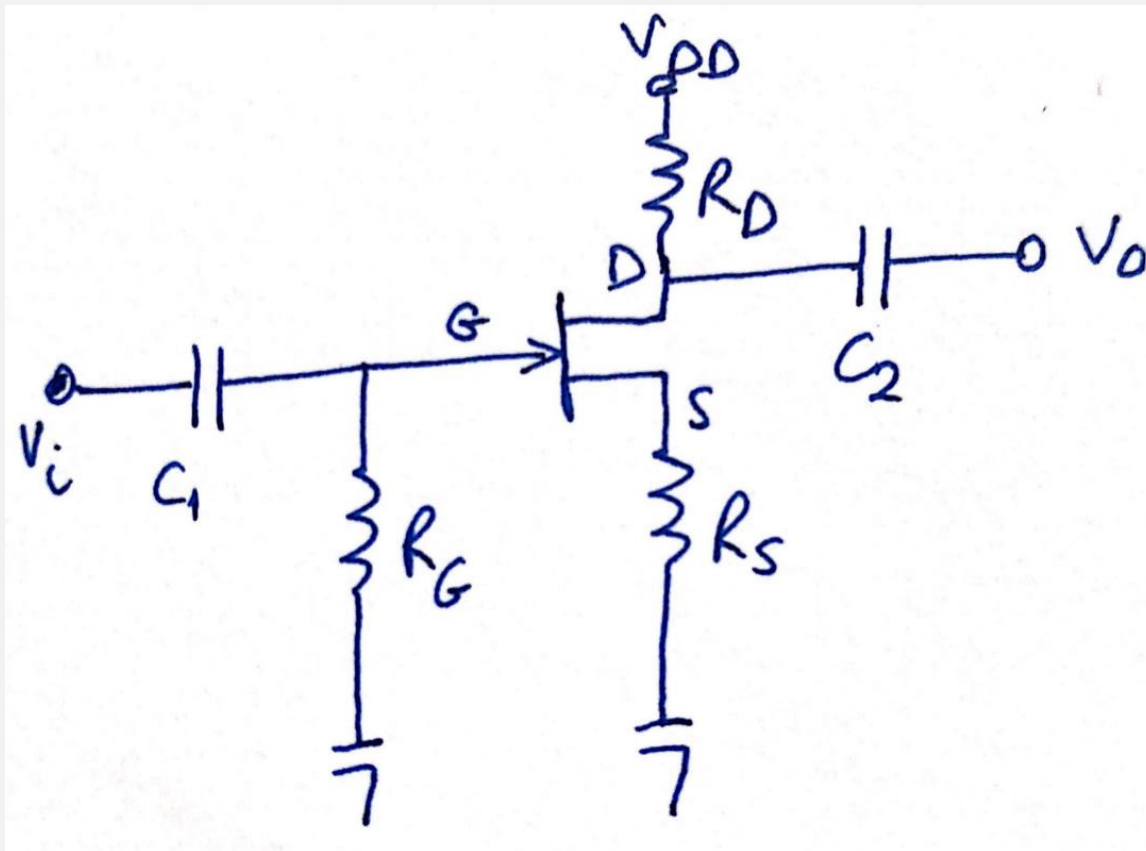
$$V_S = 0 \text{ V}$$

$$V_C = V_{DS}$$

$$V = V_{GS}$$

$$V_{GS} = -V_{GG}$$

Self-Bias Configuration



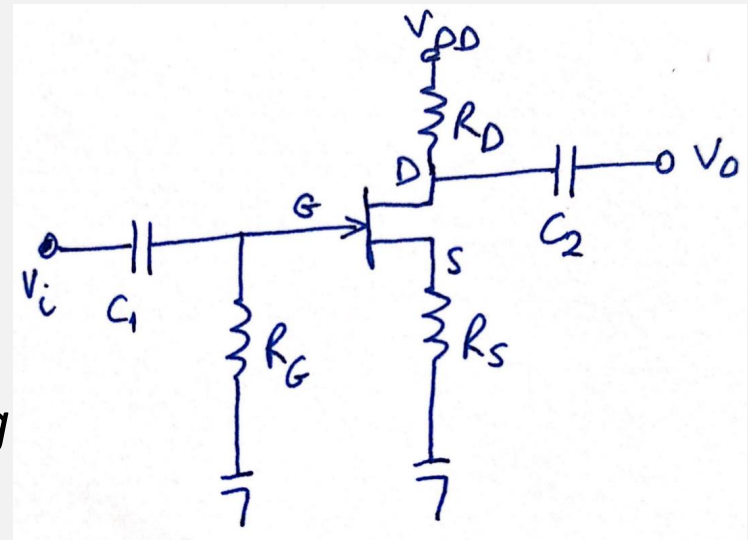
Self-Bias Calculations

$$V_{GS} = -I_D R_S$$

1. Select a value of $I_D < I_{DSS}$ and use the component value of R_S to calculate V_{GS} . Plot the point identified by I_D and V_{GS} and draw a line from the origin of the axis to this point.

2. Plot the transfer curve using I_{DSS} and V_P ($V_P = |V_{GSoff}|$ on spec sheets) and a few points such as $V_{GS} = V_P / 4$ and $V_{GS} = V_P / 2$ etc.

The **Q-point** is located where the first line intersects the transfer curve. Using the value of I_D at the Q-point (I_{DQ}):

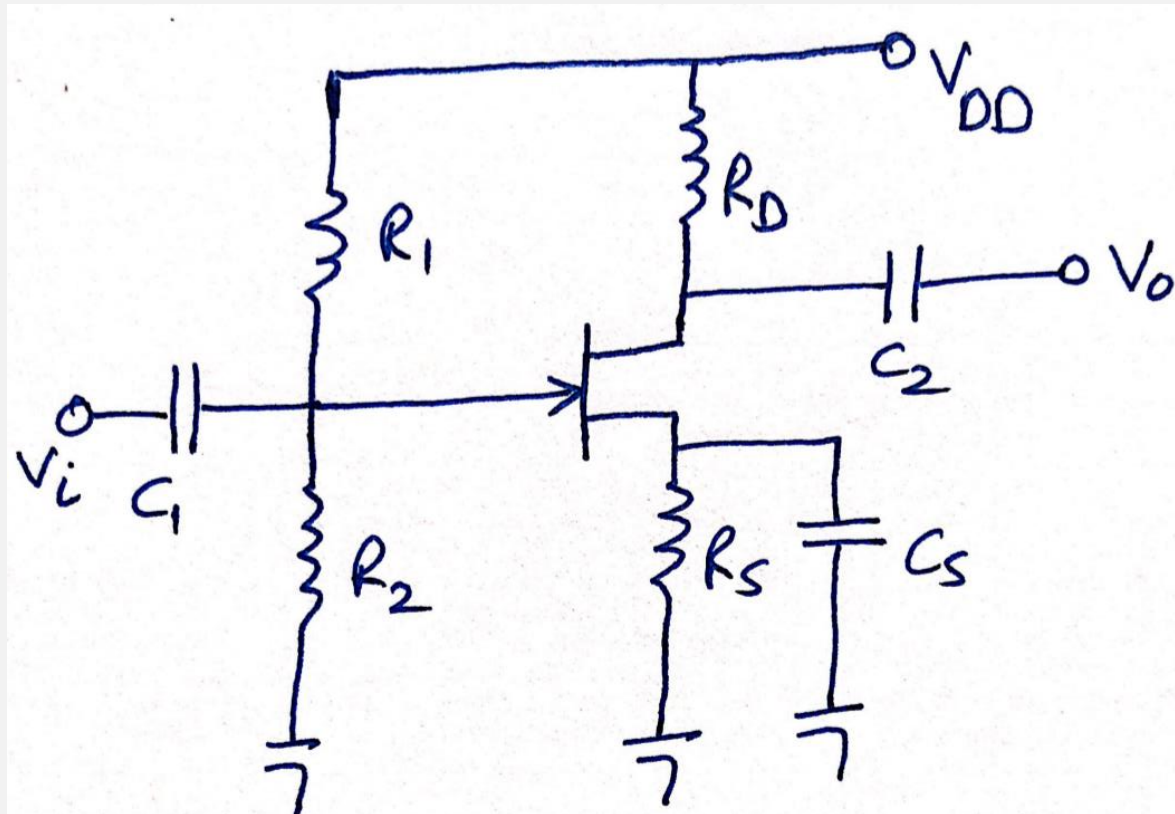


$$V_{DS} = V_{DD} - I_D (R_S + R_D)$$

$$V_S = I_D R_S$$

$$V_D = V_{DS} + V_S = V_{DD} - V_{RD}$$

Voltage-Divider Bias



- $I_G = 0 \text{ A}$
- I_D responds to changes in V_{GS}

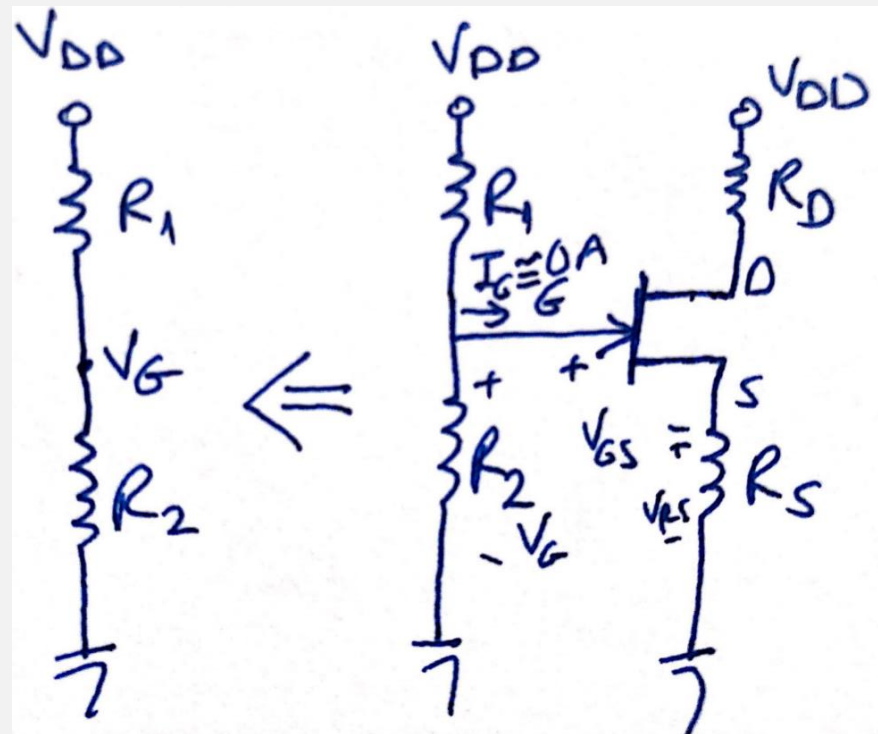
Voltage-Divider Bias Calculations

V_G is equal to the voltage across divider resistor R_2 :

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

Using Kirchhoff's Law:

$$V_{GS} = V_G - I_D R_S$$



The Q-point is established by plotting a line that intersects the transfer curve.

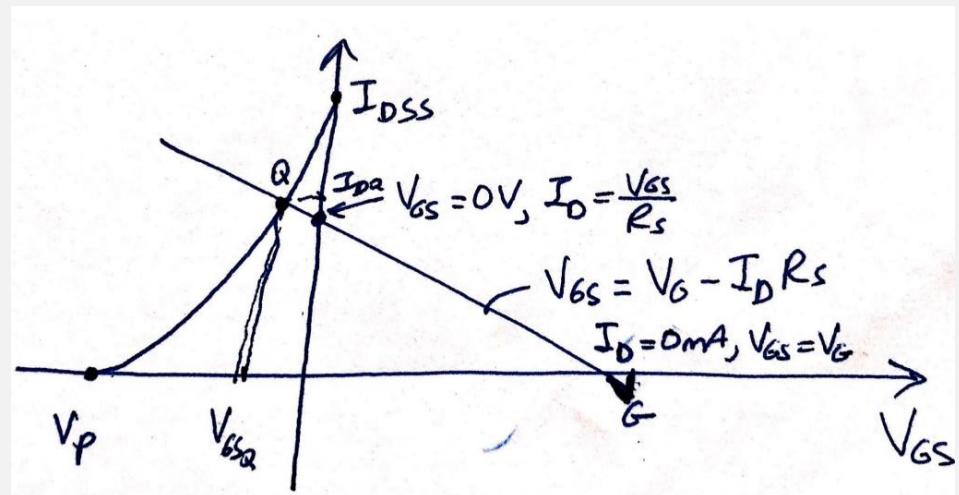
Voltage-Divider Q-Point

Plot the line that is defined by these two points:

$$V_{GS} = V_G, I_D = 0 \text{ A}$$

$$V_{GS} = 0 \text{ V}, I_D = V_G / R_S$$

Plot the transfer curve by plotting I_{DSS} , V_P and the calculated values of I_D



The Q-point is located where the line intersects the transfer curve

Voltage-Divider Bias Calculations

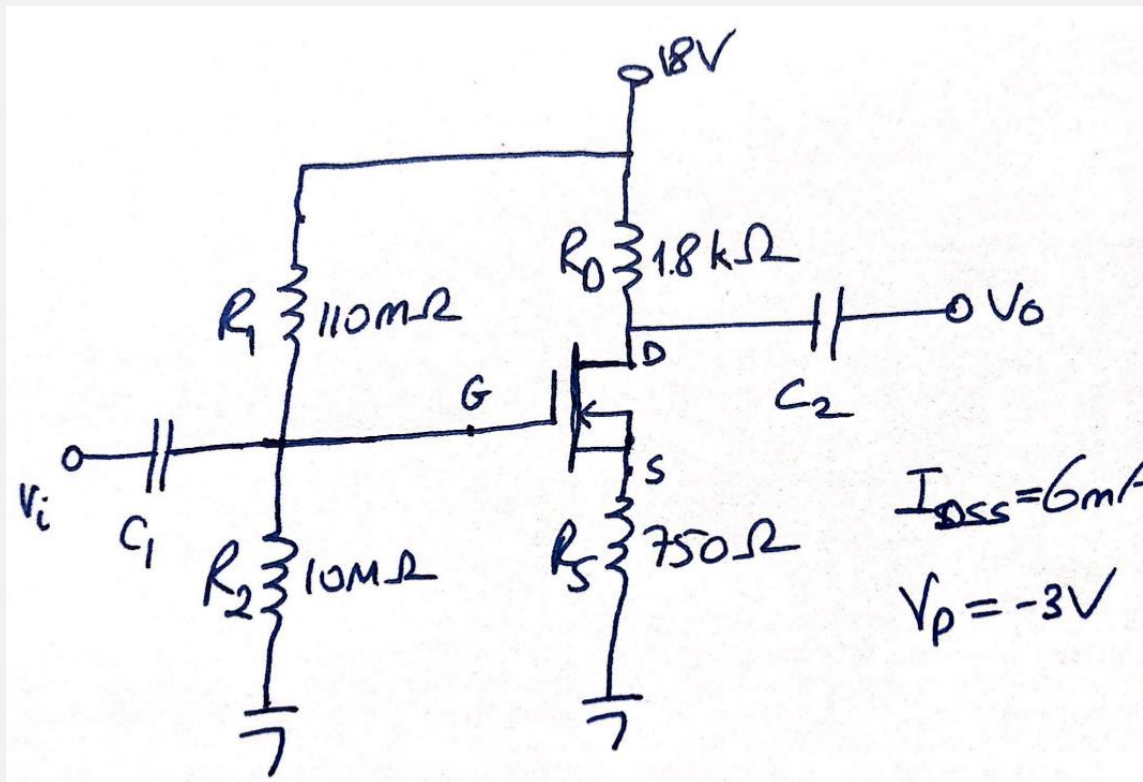
Using the value of I_D at the Q-point, solve for the other values in the voltage-divider bias circuit:

$$V_{DS} = V_{DD} - I_D (R_D + R_S)$$

$$V_D = V_{DD} - I_D R_D$$

$$V_S = I_D R_S$$

D-Type MOSFET Bias Circuits



Depletion-type MOSFET bias circuits are similar to those used to bias JFETs. The only difference is that **D-type MOSFETs can operate with positive values of V_{GS} and with I_D values that exceed I_{DSS} .**

Self-Bias Q-Point (D-MOSFET)

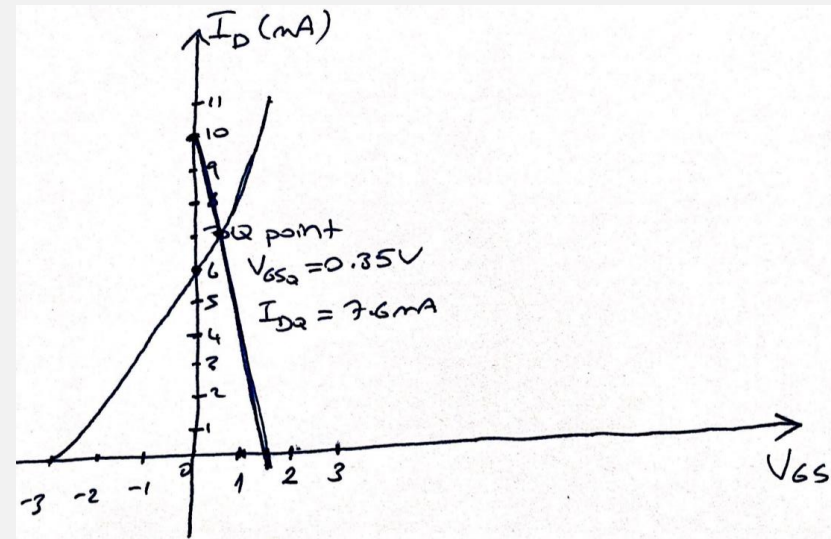
Plot the line that is defined by these two points:

$$V_{GS} = V_G, I_D = 0 \text{ A}$$

$$I_D = V_G / R_S, V_{GS} = 0 \text{ V}$$

Plot the transfer curve using I_{DSS} , V_P and calculated values of I_D .

The Q-point is located where the line intersects the transfer curve. Use the value of I_D at the Q-point to solve for the other circuit values.



*These are the same steps used to analyze **JFET self-bias** circuits.*

Voltage-Divider Bias (D-MOSFET)

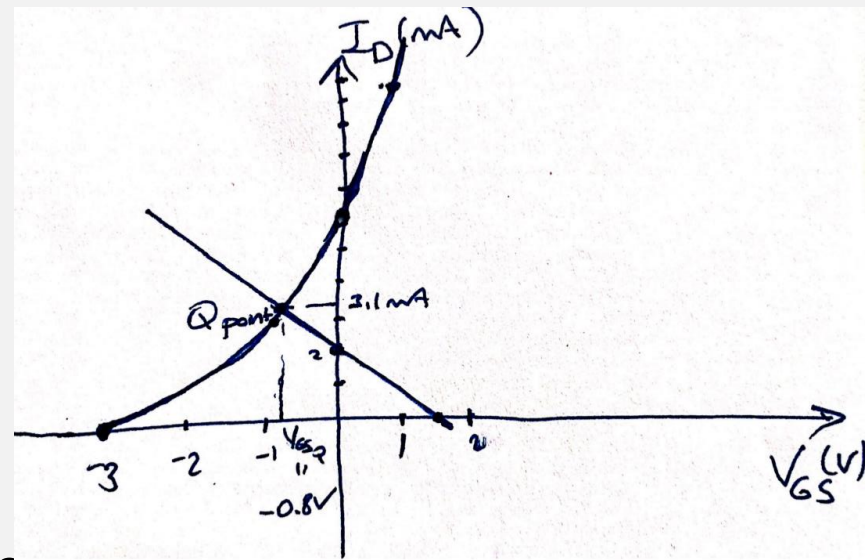
Plot the line that is defined by these two points:

$$V_{GS} = V_G, I_D = 0 \text{ A}$$

$$I_D = V_G/R_S, V_{GS} = 0 \text{ V}$$

Plot the transfer curve using I_{DSS} , V_P and calculated values of I_D .

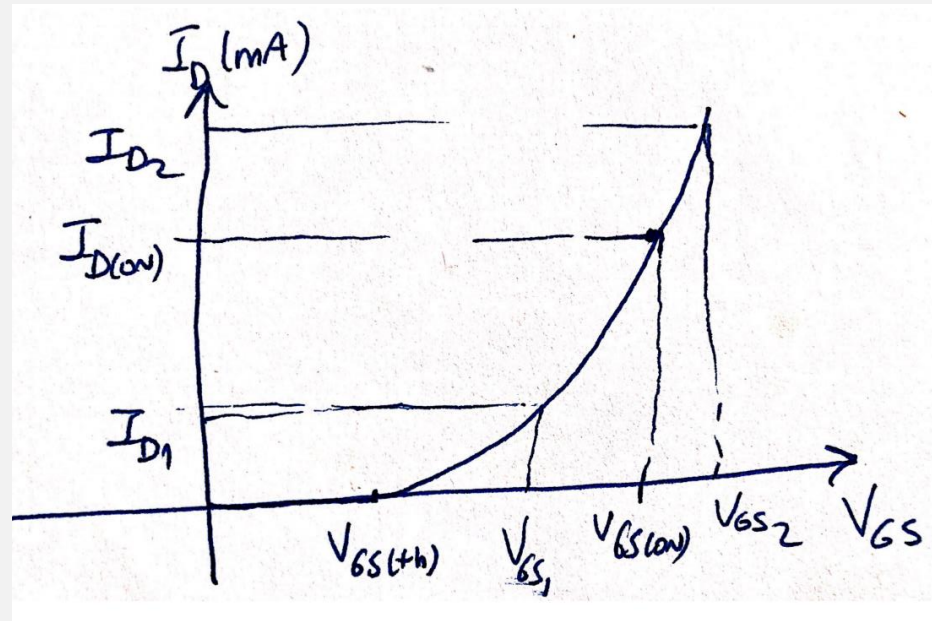
The Q-point is located where the line intersects the transfer curve. Use the value of I_D at the Q-point to solve for the other variables in the circuit.



*These are the same steps used to analyze **JFET voltage-divider bias** circuits.*

E-Type MOSFET Bias Circuits

The transfer curve for the E-MOSFET is very different from that of a simple JFET or D-MOSFET.



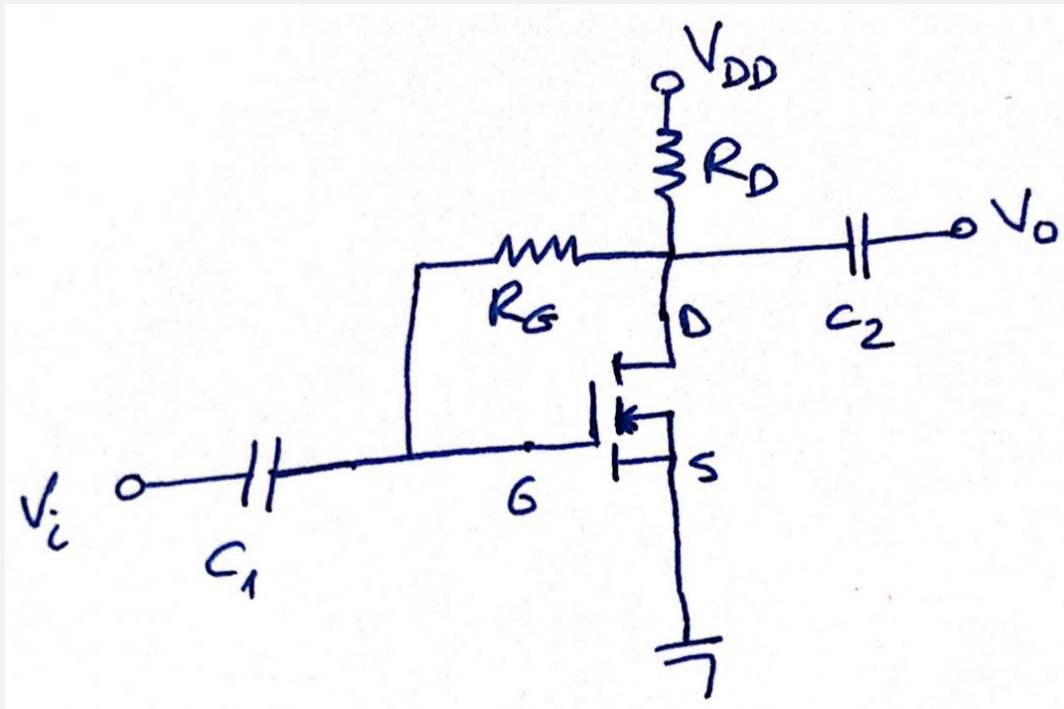
Feedback Bias Circuit (E-MOSFET)

$$I_G = 0 \text{ A}$$

$$V_{RG} = 0 \text{ V}$$

$$V_{DS} = V_{GS}$$

$$V_{GS} = V_{DD} - I_D R_D$$



Feedback Bias Q-Point (E-MOSFET)

Plot the line that is defined by these two points:

$$V_{GS} = V_{DD}, I_D = 0 \text{ A}$$

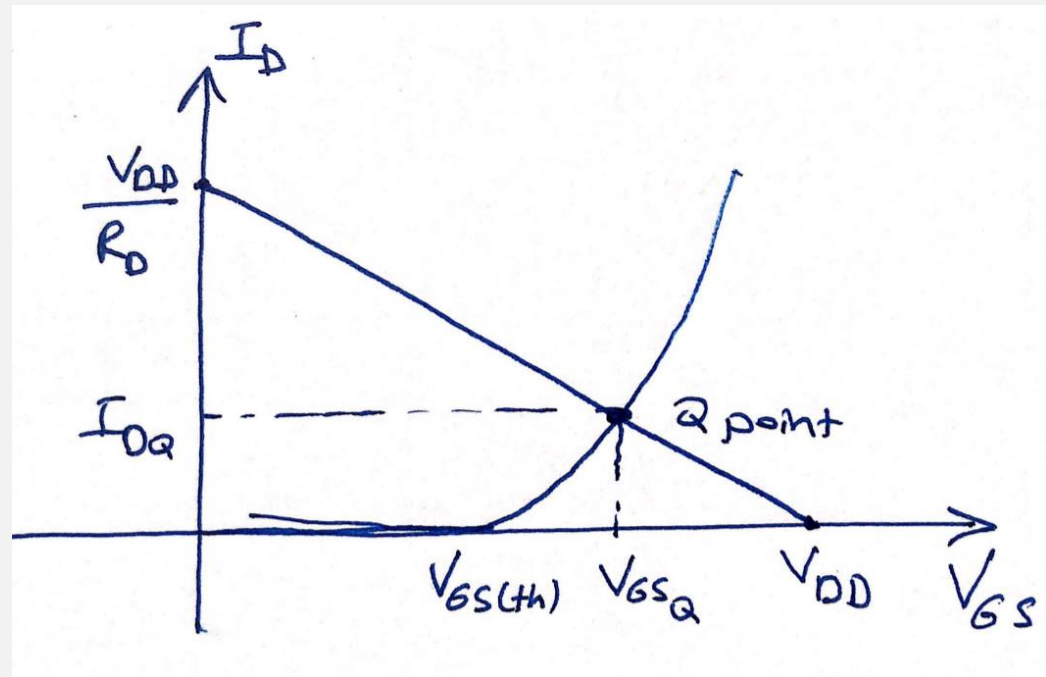
$$I_D = V_{DD} / R_D, V_{GS} = 0 \text{ V}$$

Using these values from the spec sheet, plot the transfer curve:

$$V_{GS(th)}, I_D = 0 \text{ A}$$

$$V_{GS(on)}, I_{D(on)}$$

The **Q-point** is located where the line and the transfer curve intersect



Using the value of I_D at the **Q-point**, solve for the other variables in the circuit

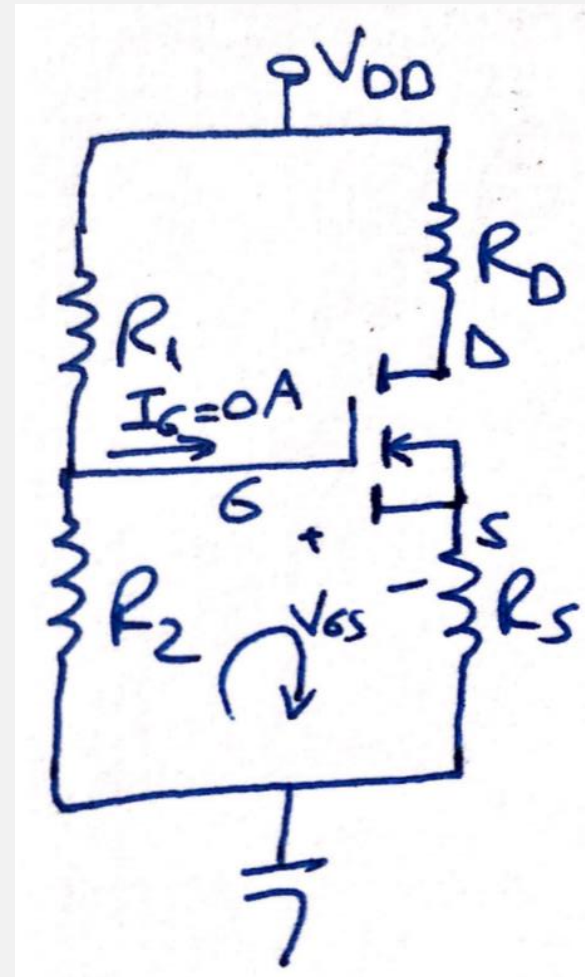
Voltage-Divider Biasing

Plot the line and the transfer curve to find the Q-point using these equations:

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

$$V_{GS} = V_G - I_D R_S$$

$$V_{DS} = V_{DD} - I_D (R_S + R_D)$$



Voltage-Divider Bias Q-Point (E-MOSFET)



Plot the line using

$$V_{GS} = V_G, I_D = 0 \text{ A}$$

$$I_D = V_G / R_S, V_{GS} = 0 \text{ V}$$

Using these values from the spec sheet, plot the transfer curve:

$$V_{GSTh}, I_D = 0 \text{ A}$$

$$V_{GS(on)}, I_{D(on)}$$

The point where **the line and the transfer curve intersect** is the **Q-point**.

Using the value of **I_D at the Q-point**, solve for the other circuit values.

p-Channel FETs

For p -channel FETs the same calculations and graphs are used, except that the voltage polarities and current directions are reversed.

The graphs are mirror images of the n -channel graphs.

Applications



- Voltage-controlled resistor
- JFET voltmeter
- Timer network
- Fiber optic circuitry
- MOSFET relay driver